



37 CFR 1.501  
 INFORMATION DISCLOSURE STATEMENT  
 IN A PATENT  
 (use several sheets if necessary)

Docket No. P97.0322 Serial No. 08/809,463

Applicants Nakamura et al.

Filing Date April 21, 1997 Group Art Unit

**U.S. PATENT DOCUMENTS**

Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate
MK	AA	4,833,042	5/23/89	Waldrop et al.			
MK	AB	5,089,738	2/18/92	Katz			
MK	AC	5,027,187	6/25/91	O'Mara, Jr. et al.			
	AD						RECEIVED
	AE						
	AF						DEC 00 1997
	AG						GROUP 2500
	AH						
	AI						
	AJ						
	AK						

**FOREIGN PATENT DOCUMENTS**

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							
	AR							
	AS							

**OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

MK	AT	IEEE ELECTRON DEVICE LETTERS, vol. EDL6, no. 8, August 1985, pp. 437-438, XP002033693, R.D. Remba et al., "Use of TiN barrier to improve GaAs FET ohmic contact reliability".
MK	AU	JOURNAL OF APPLIED PHYSICS, vol. 68, no. 5, September 1, 1990, pp. 2475-2481, XP000108786, Kim H.-J et al. "Thermally Stable Ohmic Contacts To N-Type GAAS. VIII Sputter-Deposited INAS Contacts."
	AV	
	AW	

Examiner *M. Kelley* Date Considered

2/98

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.